

EAST - [default1.wsp:1]

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Drafts BRS: Pending Active Failed Saved Favorites Tagged (11) UDC Queue Trash

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6399208 B	20030325	19	Chemical vapor deposition precursor composition for forming a metal silicate		
2	<input type="checkbox"/>	<input checked="" type="checkbox"/>	WO 200179578 A	20011025	29	New hexacoordinated silicon beta-diketonate compound is used for low		
3	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20020043666 A	20030416	14	Formation of insulation layer on semiconductor substrate comprises		
4	<input type="checkbox"/>	<input checked="" type="checkbox"/>	JP 11135774 A	19990521	46 ✓	HIGH-DIELECTRIC CONSTANT SILICATE GATE DIELECTRIC		
5	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6291283 B1	20010918	5 ✓	Method to form silicates as high dielectric constant materials	438/216	257/E21.274; 257/E21.625;
6	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6399208 B1	20020604	19	Source reagent composition and method for chemical vapor deposition formation	428/446	106/1.12; 106/1.22;
7	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6544875 B1	20030408	6 ✓	Chemical vapor deposition of silicate high dielectric constant materials	438/591	438/216; 438/287;
8	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20010021589 A1	20010913	6 ✓	Method to form silicates as high dielectric constant materials	438/778	257/E21.193; 257/E21.274;
9	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20020005556 A1	20020117	10	SILICATE GATE DIELECTRIC	257/381	257/382; 257/383;
10	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20030017715 A1	20030123	9	Composite gate dielectric layer	438/763	438/787; 438/788;
11	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20030139026 A1	20030724	10 ✓	Methods of forming binary noncrystalline oxide analogs of silicon dioxide	438/591	257/310; 438/585

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Drafts BRS Pending Active L1: (3722) (zirconium hafnium) adj silicate
L2: (378786) 1 and gate dielectric
L3: (76) 1 and (gate adj dielectric)

Failed Saved Favorites Tagged (3) UDC Queue

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Buttons: BRS term 88K term Image Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6348373 B1	20020219	3	Method for improving electrical properties of high dielectric constant films	438/240	257/E21.272; 438/253;
2	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6383873 B1	20020507	5	Process for forming a structure	438/287	438/761; 438/762
3	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6573160 B2	20030603	10	Method of recrystallizing an amorphous region of a semiconductor	438/480	438/198; 438/583

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